

Electrical Features

- Trench/Fieldstop IGBT
- Half-bridge
- Standard package
- High short circuit capability
- Including anti-parallel FWD



Typical Applications

- Frequency converter
- UPS
- Motor Drives

IGBT, Inverter

Maximum Rated Values						
Symbol	Item	Conditions	Rating			Unit
IGBT						
V_{CES}	Collector-emitter voltage	$T_{vj}=25^{\circ}\text{C}$	1200			V
V_{GES}	Gate-emitter voltage	-	± 20			V
I_C	Collector current,DC	$T_C=100^{\circ}\text{C}, T_{vj}=175^{\circ}\text{C}$	300			A
I_{CRM}	Repetitive peak collector current	$t_p=1\text{ms}$	600			A
t_{SC}	Short circuit withstand time	$V_{GE}=15\text{V}, V_{CC}=600\text{V}, T_{vj}\leq 150^{\circ}\text{C}$	10			μs
P_{tot}	Total power dissipation	$T_C=25^{\circ}\text{C}, T_{vj}=175^{\circ}\text{C}$	1612			W
Characteristics Values						
Symbol	Item	Conditions	Values			Unit
			Min.	Typ.	Max.	
I_{CES}	Collector-emitter cut-off current	$V_{CE}=1200\text{V}, V_{GE}=0\text{V}, T_{vj}=25^{\circ}\text{C}$	-	-	1	mA
I_{GES}	Gate leakage current	$V_{CE}=0\text{V}, V_{GE}=20\text{V}, T_{vj}=25^{\circ}\text{C}$	-	-	250	nA
$V_{GE(th)}$	Gate-emitter threshold voltage	$I_C=11.5\text{mA}, V_{CE}=V_{GE}, T_{vj}=25^{\circ}\text{C}$	5	5.86	7	V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=300\text{A}$ $V_{GE}=15\text{V}$ $T_{vj}=25^{\circ}\text{C}$	-	1.75	-	
		$T_{vj}=125^{\circ}\text{C}$	-	2.08	-	
		$T_{vj}=150^{\circ}\text{C}$	-	2.13	-	
C_{ies}	Input capacitance	$V_{CE}=25\text{V}, V_{GE}=0\text{V}$	-	19.4	-	nF
C_{res}	Reverse transfer capacitance	$f=1\text{MHz}, T_{vj}=25^{\circ}\text{C}$	-	0.6	-	
Q_G	Gate charge	$V_{CC}=600\text{V}, I_C=300\text{A}, V_{GE}=15\text{V}$	-	2.4	-	μC

$t_{d(on)}$	Turn-on delay time	$V_{CC}=600V,$ $I_C=300A,$ $V_{GE}=\pm 15V,$ $R_{G(on)}=5.1 \Omega,$ $R_{G(off)}=2 \Omega,$ Inductive load $di/dt=3880A/\mu s$ ($T_{vj}=150^\circ C$) $du/dt=6555V/\mu s$ ($T_{vj}=150^\circ C$)	$T_{vj}=25^\circ C$	-	109.6	-	ns
			$T_{vj}=125^\circ C$	-	262.4	-	
			$T_{vj}=150^\circ C$	-	263.2	-	
t_r	Rise time		$T_{vj}=25^\circ C$	-	112	-	
			$T_{vj}=125^\circ C$	-	111.2	-	
			$T_{vj}=150^\circ C$	-	112	-	
$t_{d(off)}$	Turn-off delay time		$T_{vj}=25^\circ C$	-	387.2	-	
			$T_{vj}=125^\circ C$	-	448.0	-	
			$T_{vj}=150^\circ C$	-	454.4	-	
t_f	Fall time	$T_{vj}=25^\circ C$	-	108	-		
		$T_{vj}=125^\circ C$	-	167.2	-		
		$T_{vj}=150^\circ C$	-	181	-		
E_{on}	Turn-on energy (per pulse)	$T_{vj}=25^\circ C$	-	30.67	-	mJ	
		$T_{vj}=125^\circ C$	-	41.6	-		
		$T_{vj}=150^\circ C$	-	43.8	-		
E_{off}	Turn-off energy (per pulse)	$T_{vj}=25^\circ C$	-	25.5	-		
		$T_{vj}=125^\circ C$	-	31.9	-		
		$T_{vj}=150^\circ C$	-	33	-		
SC data	Short-circuit current	$V_{CC}=900V, V_{GE}\leq 15V,$ $t_p\leq 10\mu s$	$T_{vj}=25^\circ C$	-	2299	-	A
			$T_{vj}=150^\circ C$	-	1914	-	
R_{thJC}	Thermal resistance, junction to case	per IGBT	-	-	0.093	-	K/W
R_{thCH}	Thermal resistance, case to heatsink	per IGBT/ $\lambda_{grease}=1W/(m\cdot K)$	-	0.032	-	-	K/W
T_{vjop}	Temperature under switching conditions		-40	-	150	-	$^\circ C$

Diode, Inverter

Maximum Rated Values

Symbol	Item	Conditions	Rating	Unit	
V_{RRM}	Repetitive peak reverse voltage	$T_{vj}=25^\circ C$	1200	V	
I_F	Forward current, DC		300	A	
I_{FRM}	Repetitive peak forward current	$t_p=1ms$	600	A	
$I^2 t$	$I^2 t$ -value	$V_R = 0 V, t_P = 10 ms,$ $V_R = 0 V, t_P = 10 ms,$	$T_{vj}=25^\circ C$	-	A^2s
			$T_{vj}=150^\circ C$	-	A^2s

Characteristic Values

V_F	Continuous forward voltage	$I_F=300A$ $V_{GE}=0V$	$T_{vj}=25^\circ C$	-	2	-	V
			$T_{vj}=125^\circ C$	-	1.57	-	
			$T_{vj}=150^\circ C$	-	1.50	-	
I_{RM}	Peak reverse recovery current	$V_R=600V$ $I_F=300A$	$T_{vj}=25^\circ C$	-	175.5	-	A
			$T_{vj}=125^\circ C$	-	290.7	-	
			$T_{vj}=150^\circ C$	-	310.5	-	
t_{rr}	Reverse recovery time	$di_F/dt=-4339A/\mu s$	$T_{vj}=25^\circ C$	-	123.9	-	ns
			$T_{vj}=125^\circ C$	-	225.8	-	
			$T_{vj}=150^\circ C$	-	241.2	-	

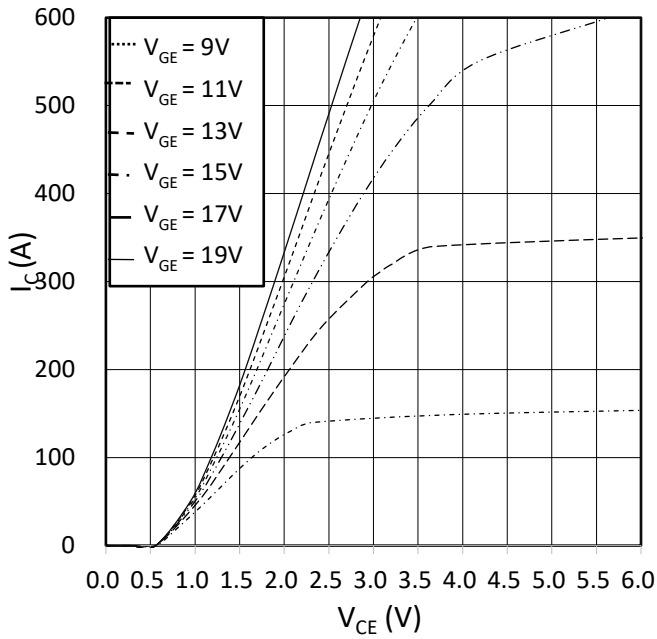
Q _r	Repetitive peak forward current		T _{vj} =25°C	-	12.29	-	μC
			T _{vj} =125°C	-	45	-	
			T _{vj} =150°C	-	51.8	-	
E _{rec}	Recovered charge		T _{vj} =25°C	-	4.51	-	mJ
			T _{vj} =125°C	-	18.57	-	
			T _{vj} =150°C	-	21.35	-	
R _{thJC}	Thermal resistance, junction to case	per diode	-	-	0.15	-	K/W
R _{thCH}	Thermal resistance, case to heatsink	per diode/ λgrease=1W/(m·K)	-	0.052	-	-	K/W
T _{vjop}	Temperature under switching conditions		-40		150		°C

Module

Symbol	Item	Conditions	Rating			Unit
V _{ISOL}	Isolation voltage	Terminals to baseplate, RMS, f=50Hz, t=1min	2500			V
-	Material of module baseplate	-	Cu			-
-	Internal isolation	Basic insulation(class 1, IEC 61140)	Al ₂ O ₃			-
CTI	Comperative tracking index	-	>200			
Symbol	Item	Conditions	Values			Unit
			Min.	Typ.	Max.	
M	Mounting torque for module mounting	Screw M6	3.0	-	6.0	Nm
	Terminal connection torque	Screw M6	2.5	-	5.0	Nm
T _{stg}	Storage temperature	-	-40	-	150	°C
RCC'+EE'		TC = 25°C, per switch	-	0.75	-	mΩ
RthCH	Thermal resistance , case to heatsink	λPaste=1W/(m·K)/λgrease=1W/(m·K)	-	-	-	K/W
LsCE	Stray inductance module		-	22	-	nH
ds	Creepage distance	Terminal to terminal	-	23	-	mm
		Terminal to base plate	-	29	-	
da	Clearance	Terminal to terminal	-	11	-	mm
		Terminal to base plate	-	23	-	
m	Weight	-	-	315	-	g

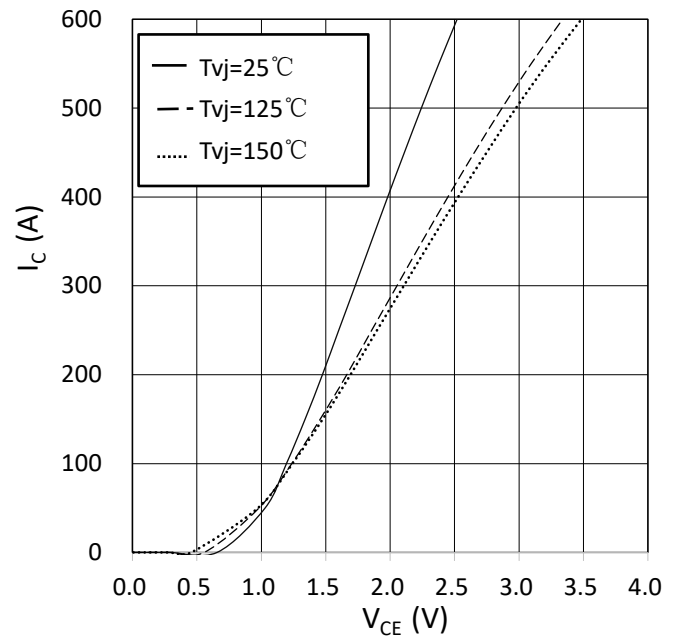
output characteristic IGBT, Inverter (typical)

$I_C = f(V_{CE})$
 $T_{vj} = 150^\circ\text{C}$



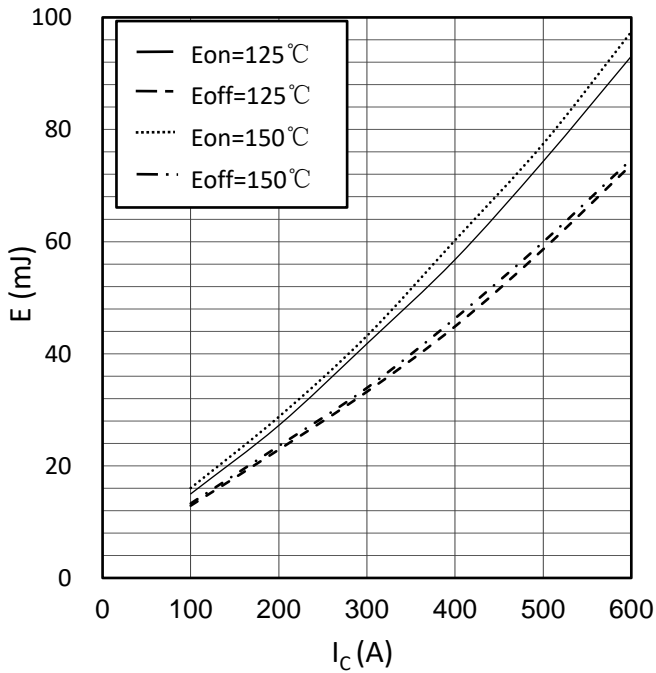
output characteristic IGBT, Inverter (typical)

$I_C = f(V_{CE})$
 $V_{GE} = 15\text{ V}$



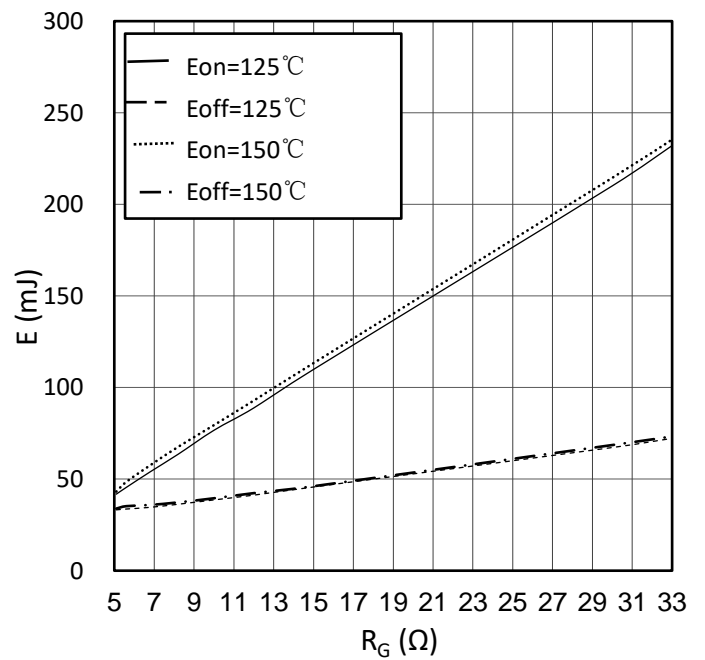
switching losses IGBT, Inverter (typical)

$E_{on} = f(I_C)$, $E_{off} = f(I_C)$
 $V_{GE} = \pm 15\text{V}$, $R_{Gon} = 5.1\Omega$, $R_{Goff} = 5.1\Omega$, $V_{CE} = 600\text{V}$



switching losses IGBT, Inverter (typical)

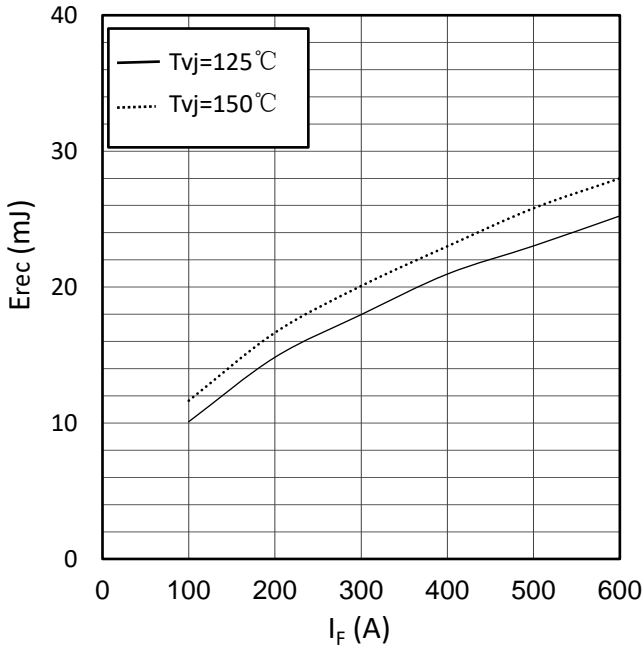
$E_{on} = f(R_G)$, $E_{off} = f(R_G)$
 $V_{GE} = \pm 15\text{V}$, $I_C = 300\text{A}$, $V_{CE} = 600\text{V}$



switching losses Diode, Inverter (typical)

$E_{rec} = f(I_F)$

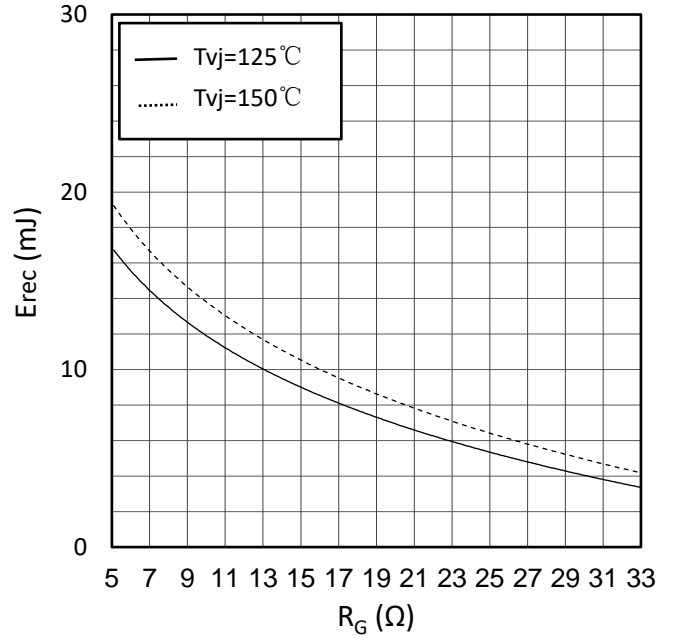
$R_{Gon}=5.1\Omega, V_{CE}=600V$



switching losses Diode, Inverter (typical)

$E_{rec} = f(R_G)$

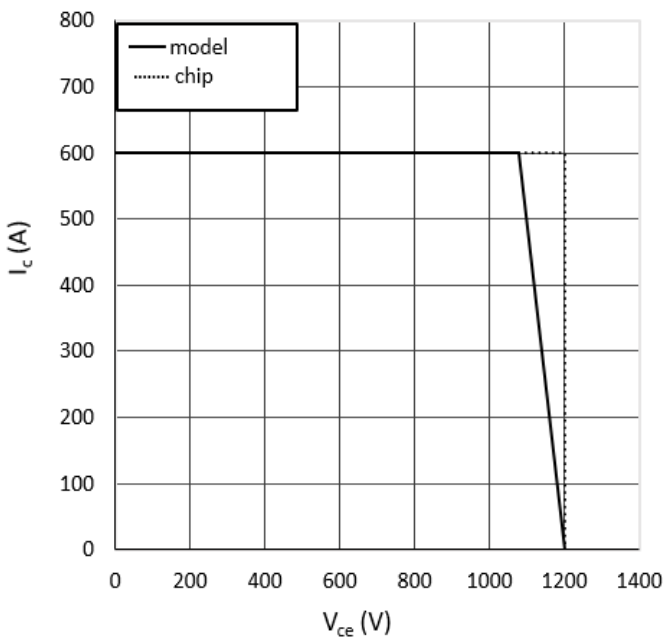
$R_{Gon}=5.1\Omega, V_{CE}=600V$



reverse bias safe operating area IGBT,Inverter (RBSOA)

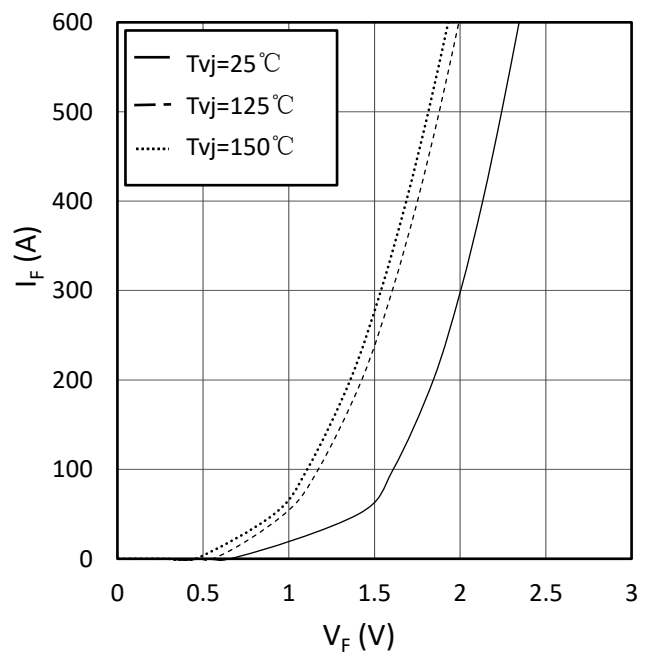
$I_C = f(V_{CE})$

$V_{GE} = \pm 15V, R_{Gon} = 5.1\Omega, R_{Goff} = 5.1\Omega, T_{vj} = 150^\circ C$

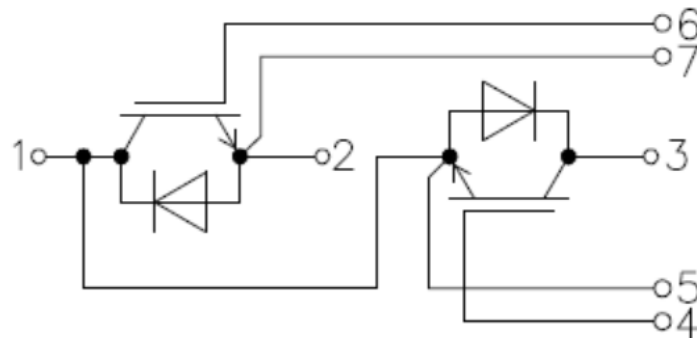


forward characteristic of Diode, Inverter (typical)

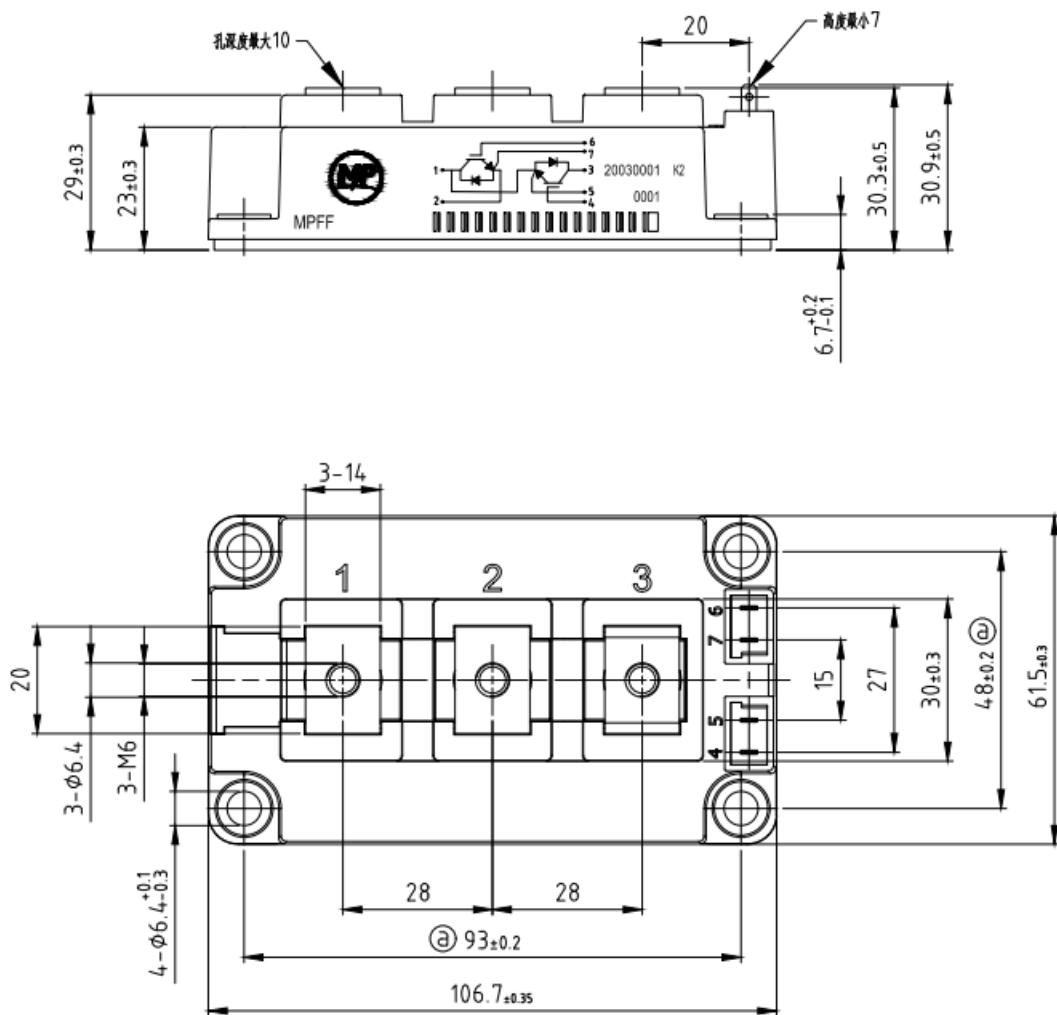
$I_F = f(V_F)$



Circuit diagram headline



Package outlines (Unit: mm)



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序号 Item	日期 Date	变更记录及描述 Change History Description	版本序号 Rev. item	经办人 Responsibility
1	2022.3.01	初版规格书发布，版本为V1.0	2022 3 Ver1.0	马慧明
2	2023.10.19	更新曲线及高温数据，版本为V1.1	2023 10Ver1.1	张成宇